



**WBFBP-02C Plastic-Encapsulate Diodes**

**DSS40LED02** Schottky Barrier Diode

**DESCRIPTION**

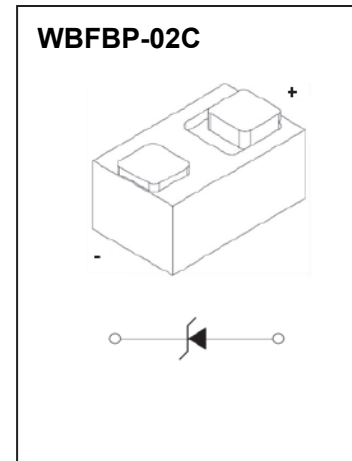
Planar Schottky barrier diode with an integrated guard ring for stress protection.

**FEATURES**

- Low diode capacitance
- Low forward voltage
- Guard ring protected

**APPLICATION**

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Mobile communication ,digital (still) cameras , PDAs and PCMCIA cards



**MARKING: S6**

**Maximum Ratings and Electrical Characteristics, Single Diode @T<sub>A</sub>=25°C**

Parameter	Symbol	Limits	Unit
DC reverse voltage	V <sub>R</sub>	40	V
Continuous forward current	I <sub>F</sub>	120	mA
Non-repetitive peak forward current(t <sub>p</sub> ≤10ms)	I <sub>FSM</sub>	200	mA
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-65~+150	°C

**Electrical Ratings @T<sub>A</sub>=25°C**

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Continuous forward voltage	V <sub>F</sub>			0.38	V	I <sub>F</sub> =1mA
				0.5		I <sub>F</sub> =10mA
				1		I <sub>F</sub> =40mA
Continuous reverse current (note 1)	I <sub>R</sub>			1	µA	V <sub>R</sub> =30V
				10		V <sub>R</sub> =40V
Diode capacitance	C <sub>d</sub>			5	pF	V <sub>R</sub> =0V, f=1MHz

Note:

1. pulse test: t<sub>p</sub>=300µs; δ=0.02

# Typical Characteristics

# DSS40LED02

